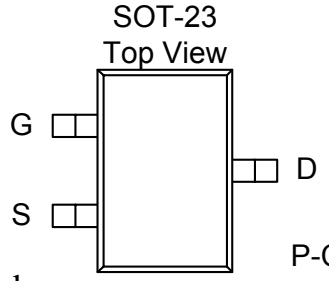
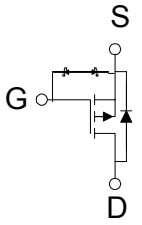
P - Channel 40V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-40	0.164 @ V_{GS} = -10 V	-3.2
	0.260 @ V_{GS} = -4.5V	-2.6

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOT-23 saves board space
- Fast switching speed
- High performance trench technology





P-Channel MOSFET

ESD Protected
2000V

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		**Symbol**	**Ratings**	**Units**
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current[a]	T_A=25°C	I_D	± 3.2	A
	T_A=70°C		± 2.7	
Pulsed Drain Current[b]		I_{DM}	±10	
Continuous Source Current (Diode Conduction)[a]		I_S	0.4	A
Power Dissipation[a]	T_A=25°C	P_D	1.25	W
	T_A=70°C		0.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter		**Symbol**	**Maximum**	**Units**
Maximum Junction-to-Ambient[a]	t <= 5 sec	R_{THJA}	100	°C/W
	Steady-State		150	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

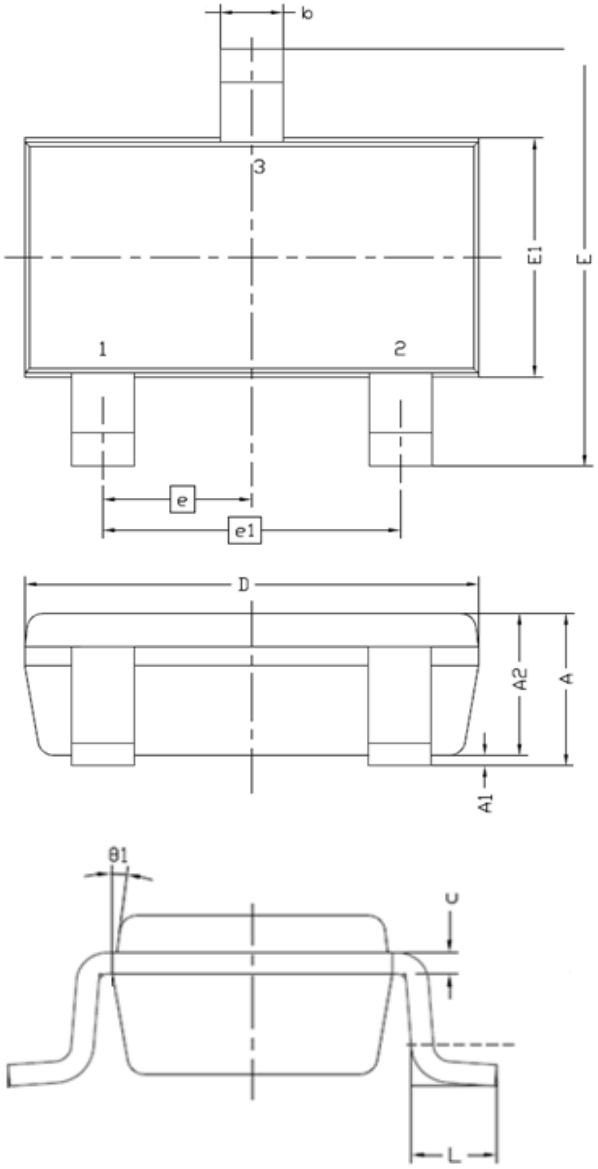
SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Switch Off Characteristics						
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -32 V, V_{GS} = 0 V			-1	μA
		V_{DS} = -32 V, V_{GS} = 0 V, T_J = 55°C			-10	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 uA	-1.0			V
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = -5 V, V_{GS} = -4.5 V	-2			A
Drain-Source On-Resistance[A]	$r_{DS(on)}$	V_{GS} = -10 V, I_D = -3.2 A			164	mΩ
		V_{GS} = -4.5 V, I_D = -2.6 A			260	
Forward Tranconductance[A]	g_{fs}	V_{DS} = -5 V, I_D = -3.6 A		2		S
Diode Forward Voltage	V_{SD}	I_S = -0.4 A, V_{GS} = 0 V		-0.70		V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = -10 V, V_{GS} = -5 V, I_D = -3.6 A		15		nC
Gate-Source Charge	Q_{gs}			2.0		
Gate-Drain Charge	Q_{gd}			2.0		
Turn-On Delay Time	$t_{d(on)}$	V_{DS} = -15 V, I_D = -1 A, R_G = 50Ω, V_{GEN} = -10 V		10		ns
Rise Time	t_r			2.8		
Turn-Off Delay Time	$t_{d(off)}$			53.6		
Fall-Time	t_f			46		

Notes

a. Pulse test: PW <= 300us duty cycle <= 2%.

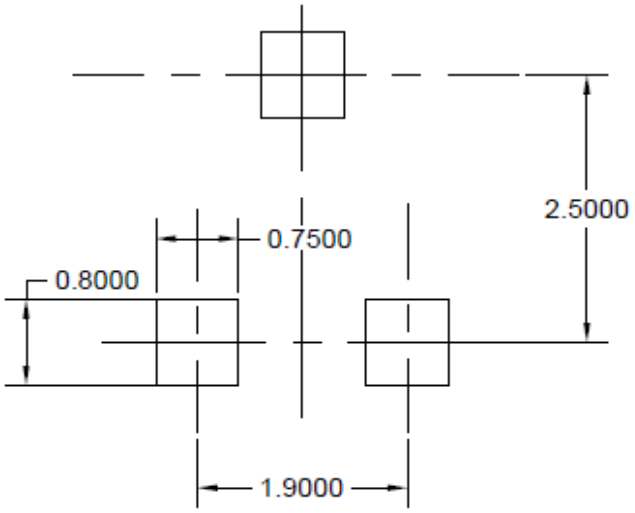
b. Guaranteed by design, not subject to production testing.

Package Information



Symbol	MILLIMETERS	
	MIN	MAX
A	0.8	1.2
A1	0	0.1
A2	0.7	1.1
b	0.3	0.5
c	0.1	0.2
D	2.7	3.1
E	2.6	3
E1	1.4	1.8
e	0.95 BSC	
e1	1.9 BSC	
L	0.3	0.6
θ1	7° NOM	

Recommended Pad Layout



Note: Drain opening is recommended to be solder mask defined in a copper fill for improved thermal performance